Silicon PNP Epitaxial

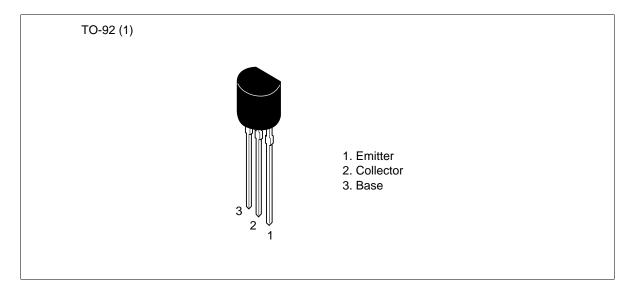
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ADE-208-1004A (Z) 2nd. Edition Mar. 2001

## Application

- Low frequency amplifier
- Complementary pair with 2SC458 and 2SC2308

### Outline





## **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	2SA1029	2SA1030	Unit
Collector to base voltage	V <sub>CBO</sub>	-30	-55	V
Collector to emitter voltage	V <sub>CEO</sub>	-30	-50	V
Emitter to base voltage	V <sub>EBO</sub>	-5	-5	V
Collector current	I <sub>c</sub>	-100	-100	mA
Emitter current	I <sub>E</sub>	100	100	mA
Collector power dissipation	Pc	300	300	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

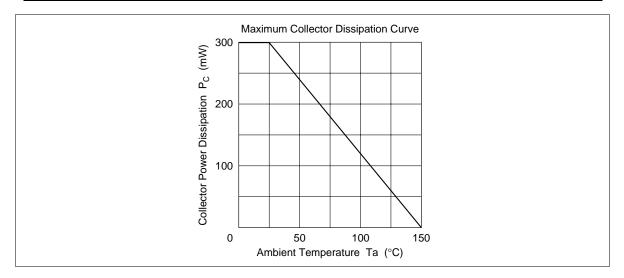
## **Electrical Characteristics** (Ta = $25^{\circ}$ C)

		2SA1	029		2SA1	2SA1030			
Item	Symbol	Min	Тур	Max	Min	Тур	Мах	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-30	_	—	-55	_	—	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{\rm (BR)CEO}$	-30	_	_	-50	_	_	V	$I_c = -1 \text{ mA}, \text{ R}_{BE} = \infty$
Emitter to base breakdown voltage	$V_{\rm (BR)EBO}$	-5	_	_	-5	_	_	V	$I_{\rm E} = -10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I <sub>CBO</sub>		_	-0.5	—		-0.5	μΑ	$V_{_{CB}} = -18 \text{ V}, \text{ I}_{_{E}} = 0$
Emitter cutoff current	I <sub>EBO</sub>		_	-0.5	—		-0.5	μΑ	$V_{EB} = -2 V, I_{C} = 0$
DC current trnsfer ratio	$h_{FE}^{*1}$	100	—	500	100	—	320		$V_{ce} = -12 V,$ $I_{c} = -2 mA$
Base to emitter voltage	$V_{BE}$	—	—	-0.8	—	—	-0.8	V	$V_{ce} = -12 V,$ $I_c = -2 mA$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	—	-0.2	—	—	-0.2	V	$I_{c} = -10 \text{ mA},$ $I_{B} = -1 \text{ mA}$
Gain bandwidth product	f <sub>T</sub>	200	280	—	200	280	—	MHz	$V_{CB} = -12 V,$ $I_{C} = -2 mA$
Collector output capacitance	Cob	_	3.3	4.0	—	3.3	4.0	pF	$V_{CB} = -10 \text{ V}, I_E = 0,$ f = 1 MHz
Note: 1. The 2SA102	9 and 2SA	1030 a	re grou	ped by	h <sub>FE</sub> as i	follows.			
В	С		D						
28A1020 100 to 20	0 160 t	<u>^ 3</u> 20	250 1	0 E00					

	0	0	D
2SA1029	100 to 200	160 to 320	250 to 500
2SA1030	100 to 200	160 to 320	_

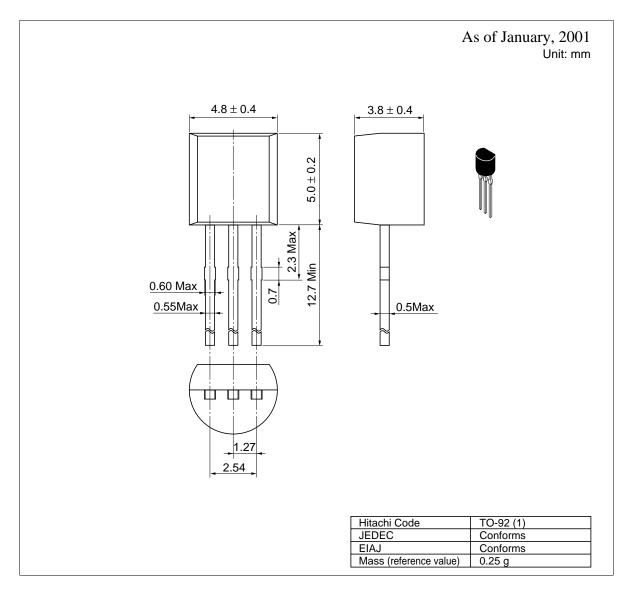
See characteristic curves of 2SA1052.

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### **Package Dimensions**



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